Product Brief
PE64101

For full datasheet, please visit dtc.psemi.com.

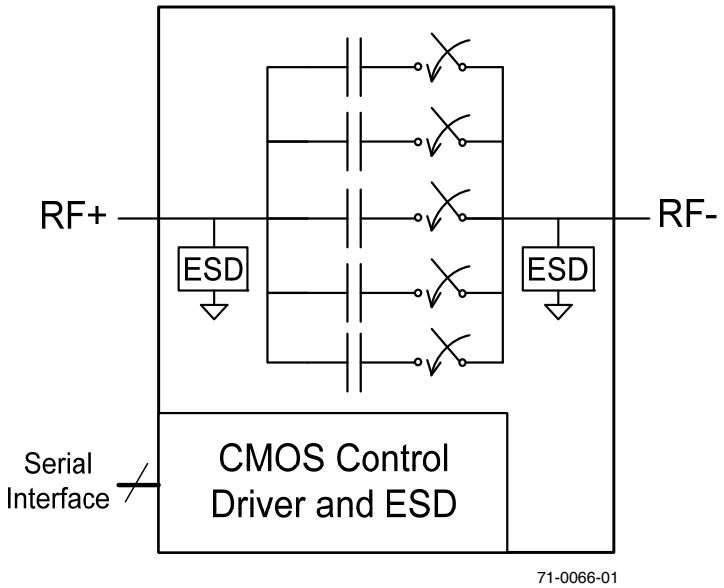
Product Description

The PE64101 is a DuNE™-enhanced Digitally Tunable Capacitor (DTC) based on Peregrine's UltraCMOS® technology. DTC products provide a monolithically integrated impedance tuning solution for demanding RF applications. They also offer a cost-effective tunable capacitor with excellent linearity and ESD performance.

This highly versatile product can be mounted in series or shunt configuration and is controlled by a 3-wire (SPI compatible) serial interface. High ESD rating of 2 kV HBM on all ports making this the ultimate in integration and ruggedness. The DTC is offered in a standard 12-lead 2.0 x 2.0 x 0.55 mm QFN package.

Peregrine's DuNE™ technology enhancements deliver high linearity and exceptional harmonics performance. It is an innovative feature of the UltraCMOS® process, providing performance superior to GaAs with the economy and integration of conventional CMOS.

Figure 1. Functional Block Diagram



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UltraCMOS® Digitally Tunable Capacitor (DTC) 100 - 3000 MHz

Features

- 3-wire (SPI compatible) 8-bit serial interface with built-in bias voltage generation and stand-by mode for reduced power consumption
- DuNE™-enhanced UltraCMOS® device
- 5-bit 32-state Digitally Tunable Capacitor
- C = 1.38 – 5.90 pF (4.3:1 tuning ratio) in discrete 146 fF steps
- RF power handling (up to 26 dBm, 6 V_{PK} RF) and high linearity
- High quality factor
- Wide power supply range (2.3 to 3.6V) and low current consumption (typ. I_{DD} = 30 µA @ 2.8V)
- Optimized for shunt configuration, but can also be used in series configuration
- Excellent 2 kV HBM ESD tolerance on all pins
- Applications include:
  - Antenna tuning
  - Tunable filters
  - Phase shifters
  - Impedance matching

Figure 2. Package Type
12-lead 2 x 2 x 0.55 mm QFN

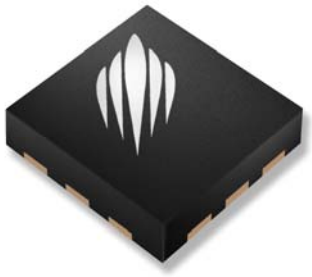


Table 1. Electrical Specifications @ 25°C, V_{DD} = 2.8V

Parameter	Configuration	Condition	Min	Typ	Max	Units
Operating Frequency Range [7]	Both		100		3000	MHz
Minimum Capacitance	Shunt [6]	State = 00000, 100 MHz (RF+ to Grounded RF-)	-10%	1.38	+10%	pF
Maximum Capacitance	Shunt [6]	State = 11111, 100 MHz (RF+ to Grounded RF-)	-10%	5.90	+10%	pF
Tuning Ratio	Shunt [6]	C_{max}/C_{min}, 100 MHz		4.3:1		
Step Size	Shunt [6]	5 bits (32 states), constant step size (100 MHz)		0.146		pF
Quality Factor (C_{min}) [1]	Shunt [6]	470 - 582 MHz with L_s removed 698 - 960 MHz, with L_s removed 1710 - 2170 MHz, with L_s removed		50 50 30		
Quality Factor (C_{max}) [1]	Shunt [6]	470 - 582 MHz with L_s removed 698 - 960 MHz, with L_s removed 1710 - 2170 MHz, with L_s removed		50 25 10		
Self Resonant Frequency	Shunt [7]	State 00000 State 11111		5.5 2.5		GHz
Harmonics (2_{fo} and 3_{fo}) [4]	Shunt [6]	470 to 582 MHz, Pin +26 dBm, 50Ω 698 to 915 MHz, Pin +26 dBm, 50Ω 1710 to 1910 MHz, Pin +26 dBm, 50Ω			-36 -36 -36	dBm dBm dBm
	Series [5]	470 to 582 MHz, Pin +20 dBm, 50Ω 698 to 915 MHz, Pin +20 dBm, 50Ω 1710 to 1910 MHz, Pin +20 dBm, 50Ω			-36 -36 -36	dBm dBm dBm
3rd Order Intercept Point	Shunt [6]	IIP3 = (Pblocker + 2*Ptx - [IMD3]) / 2, where IMD3 = -95 dBm, Ptx = +20 dBm and Pblocker = -15 dBm		60		dBm
Switching Time [2, 3]	Shunt [6]	State change to 10/90% delta capacitance between any two states		2	10	µs
Start-up Time [2]	Shunt [6]	Time from V_{DD} within specification to all performances within specification		5	20	µs
Wake-up Time [2, 3]	Shunt [6]	State change from standby mode to RF state to all performances within specification		5	20	µs

Note: 1. Q for a Shunt DTC based on a Series RLC equivalent circuit
$Q = X_C / R = (X-X_L)/R$, where $X = X_L + X_C$, $X_L = 2*pi*f*L$, $X_C = -1 / (2*pi*f*C)$, which is equal to removing the effect of parasitic inductance L_S
2. DC path to ground at RF+ and RF– must be provided to achieve specified performance
3. State change activated on falling edge of SEN following data word
4. Between 50Ω ports in series or shunt configuration using a pulsed RF input with 4620 vs period, 50% duty cycle, measured per 3GPPTS45.005
5. In series configuration the greater RF power or higher RF voltage should be applied to RF+
6. RF- should be connected to ground
7. DTC operation above SRF is possible

Figure 3. Pin Configuration (Top View)

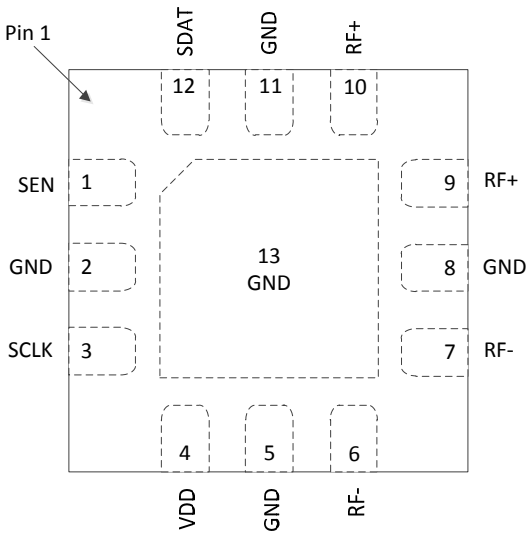


Table 2. Pin Descriptions

Pin #	Pin Name	Description
1	SEN	Serial Enable
2	GND	Digital and RF Ground
3	SCLK	Serial Interface Clock Input
4	VDD	Power Voltage
5	GND	Digital and RF Ground
6	RF-	Negative RF Port [1]
7	RF-	Negative RF Port [1]
8	GND	Digital and RF Ground [3]
9	RF+	Positive RF Port [2]
10	RF+	Positive RF Port [2]
11	GND	Digital and RF Ground
12	SDAT	Serial Interface Data Input
13	GND	Digital and RF Ground [3]

Notes: 1. Pins 6 and 7 must be tied together on PCB board to reduce inductance
2. Pins 9 and 10 must be tied together on PCB board to reduce inductance
3. Pin 2, 5, 8, 11 and 13 must be connected together on PCB

Moisture Sensitivity Level

The Moisture Sensitivity Level rating for the PE64101 in the 12-lead 2 x 2 QFN package is MSL1.

Latch-Up Avoidance

Unlike conventional CMOS devices, UltraCMOS® devices are immune to latch-up.

Table 3. Operating Ranges[1]

Parameter	Symbol	Min	Typ	Max	Units
V_{DD} Supply Voltage	V_{DD}	2.3	2.8	3.6	V
I_{DD} Power Supply Current (Normal mode) [6]	I_{DD}		30	75	µA
I_{DD} Power Supply Current (Standby mode) [6]	I_{DD}		20	45	µA
Control Voltage High	V_{IH}	1.2		3.1	V
Control Voltage Low	V_{IL}	0		0.2	V
Peak Operating RF Voltage [5] V_P to V_M V_P to RFGND V_M to RFGND				 6 6 6	 V_{PK} V_{PK} V_{PK}
RF Input Power (50Ω) [3, 4, 5] shunt series				 +26 +20	 dBm dBm
Input Control Current	I_{CTL}		1	10	µA
Operating Temperature Range	T_{OP}	-40		+85	°C
Storage Temperature Range	T_{ST}	-65		+150	°C

Notes: 1. Operation should be restricted to the limits in the Operating Ranges table
2. The DTC is active when STBY is low (set to 0) and in low-current stand-by mode when high (set to 1)
3. Maximum CW power available from a 50Ω source in shunt configuration
4. Maximum CW power available from a 50Ω source in series configuration
5. RF+ to RF- and RF+ and/or RF- to ground. Cannot exceed 6 V_{PK} or max RF input power (whichever occurs first)
6. I_{DD} current typical value is based on V_{DD} = 2.8V. Max I_{DD} is based on V_{DD} = 3.6V

Table 4. Absolute Maximum Ratings

Symbol	Parameter/Conditions	Min	Max	Units
V_{DD}	Power supply voltage	-0.3	4.0	V
V_I	Voltage on any DC input	-0.3	4.0	V
V_{ESD}	ESD Voltage (HBM, MIL_STD 883 Method 3015.7)		2000	V
V_{ESD}	ESD Voltage (MM, JEDEC JESD22-A115-A)		100	V

Exceeding absolute maximum ratings may cause permanent damage. Operation between operating range maximum and absolute maximum for extended periods may reduce reliability.

Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS® device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the specified rating.

Figure 4. Package Drawing

12-lead 2 x 2 x 0.55 mm QFN

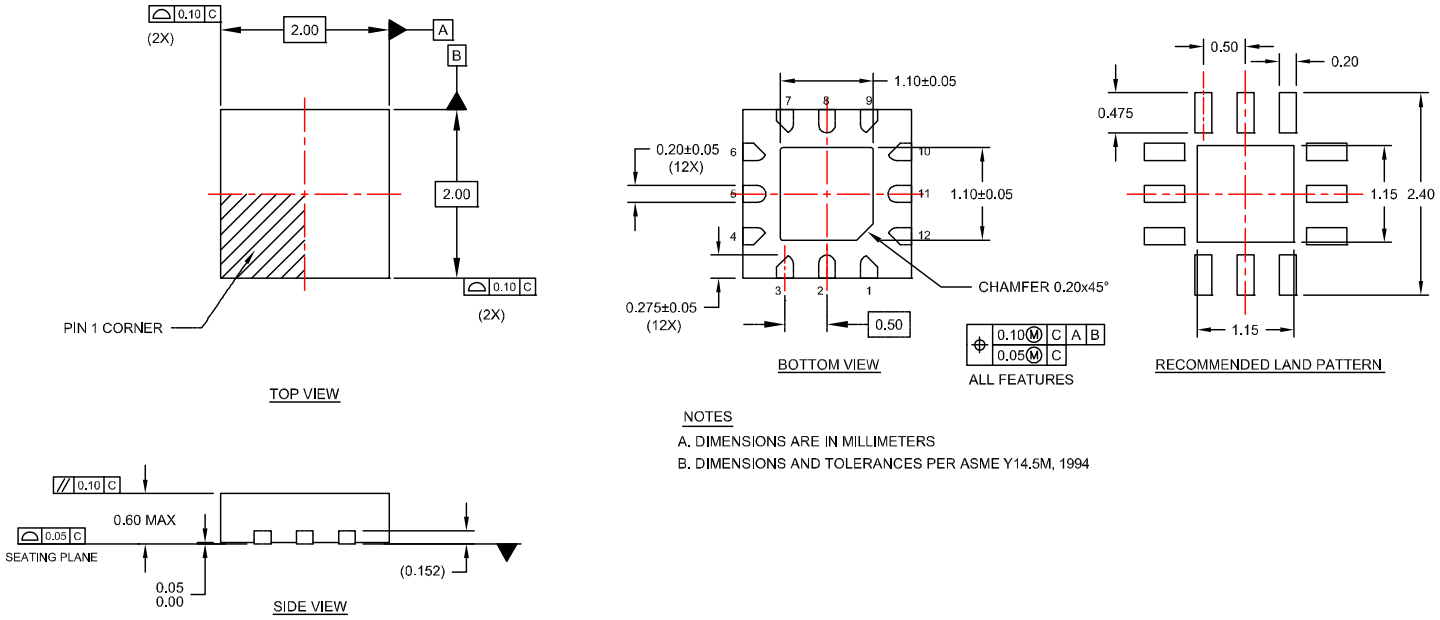
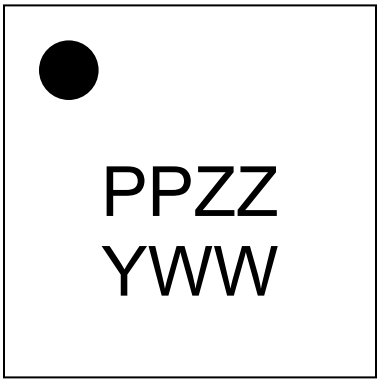


Figure 5. Top Marking Specifications

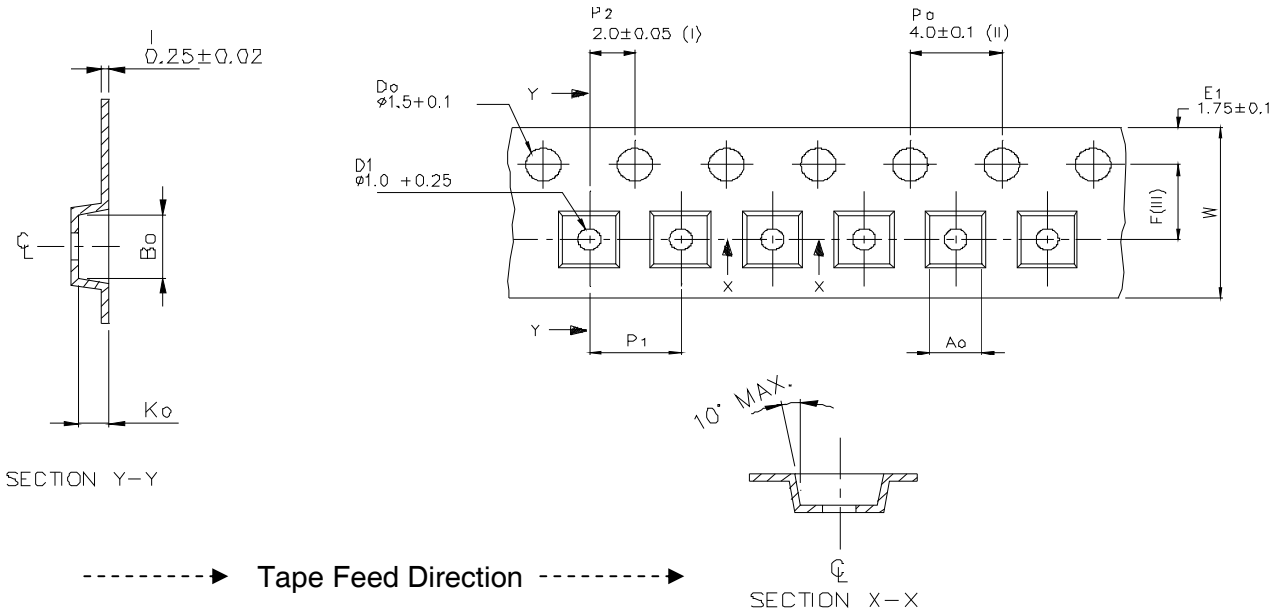


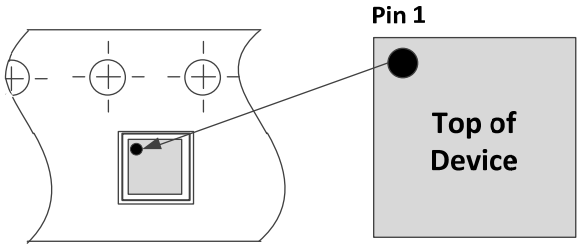
17-0112

Marking Spec Symbol	Package Marking	Definition
PP	CR	Part number marking for PE64101
ZZ	00-99	Last two digits of lot code
Y	0-9	Last digit of year, starting from 2009 (0 for 2010, 1 for 2011, etc)
WW	01-53	Work week

Figure 6. Tape and Reel Specifications

12-lead 2 x 2 x 0.55 mm QFN





Device Orientation in Tape

Table 5. Ordering Information

Order Code	Package	Description	Shipping Method
PE64101MLAA-Z	12-lead 2 x 2 x 0.55 mm QFN	Package Part in Tape and Reel	3000 units/T&R
EK64101-11	Evaluation Kit	Evaluation Kit	1 Set/Box

Sales Contact and Information

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